

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	5	("5218213" "5476813" "5759898" "5847419" "6521041").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/25 14:53
L3	365	(soi or sgoi or silicon-on-insulator or (silicon or si or semiconductor) near4 (buried near oxide or buried near insulator or box)) near8 (strained or straining or tensile or compressive or compression or strain) and (strain or straining or strained or tension or tensile or compressive or compression or relaxed or relaxation or relaxing) near5 (heat or heating or heated or anneal\$4 or temperature or thermal or thermally or rta)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/25 15:56
L4	70	(ssoi or ssdoi) and (strain or straining or strained or tension or tensile or compressive or compression or relaxed or relaxation or relaxing) near5 (heat or heating or heated or anneal\$4 or temperature or thermal or thermally or rta)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/25 15:56
L5	15	(US-20050153524-\$ or US-20020140031-\$ or US-20040253792-\$ or US-20040094763-\$ or US-20050167652-\$ or US-20050124146-\$ or US-20060030133-\$ or US-20040142541-\$ or US-20040126958-\$).did. or (US-6774015-\$ or US-7026249-\$ or US-6815802-\$ or US-6750486-\$ or US-6946373-\$).did. or (US-3272748-\$).did.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/25 16:05
L6	4	"20040087114" "20030232467" "6723541".pn. "5413679".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/25 16:11
S26	28	438/763.ccls. and (strain or strained or straining or tensile or compressive or compressed) near2 (silicon or si)	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/23 16:11
S27	151	438/938.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/23 16:19
S28	400	257/616.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/23 16:30

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S30	333	257/E29.193.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/23 16:39
S31	10	(US-20050153524-\$ or US-20040253792-\$ or US-20050124146-\$ or US-20040142541-\$ or US-20020140031-\$ or US-20050167652-\$).did. or (US-6815802-\$ or US-6750486-\$ or US-6774015-\$).did. or (US-3272748-\$).did.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/19 16:45
S32	4	"20040087114" "20030232467" "6723541".pn. "5413679".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/25 16:11
S33	428	(soi or sgoi or silicon-on-insulator) and (strained or straining or tensile) near3 (silicon or si) near8 (under or underneath or below or over or above or top or bottom or upon or higher or lower or underlying or overlying) near6 (sige or silicon near germanium or gesi or si near ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/23 08:52
S34	337	(soi or sgoi or silicon-on-insulator) near (strained or straining or strain or tensile or compressed or compressive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/23 09:28
S35	294	(soi or sgoi or silicon-on-insulator) near (strained or straining or strain or tensile or compressed or compressive) and (anneal\$4 or heat or heating or heated or cure or curing or cured or temperature or rta)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/23 09:29
S36	260	(ssoi or strained adj silicon-on-insulator or strained adj soi)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/23 13:55
S37	184	(soi or sgoi or silicon-on-insulator) and (strained or straining or tensile) near3 (silicon or si) near8 (under or underneath or below or over or above or top or bottom or upon or higher or lower or underlying or overlying) near6 (sige or silicon near germanium or gesi or si near ge) and (etch\$4 or remov\$4) near3 (sige or gesi or si near ge or silicon near germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/23 14:16

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S38	169	(soi or sgoi or silicon-on-insulator) and (strained or straining or tensile) near3 (silicon or si) near6 (sige or silicon near germanium or gesi or si near ge) and (straining or strained or strain or tensile) near6 (anneal or annealing or annealed)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/23 14:32
S39	83	("20010009784" "20020074598" "20020086472" "20020086497" "20020090791" "20030032261" "20030040158" "20030057184" "20030067035" "20040087119" "20040142541" "20050098829" "3602841" "4665415" "4853076" "4855245" "4952524" "4958213" "5006913" "5060030" "5081513" "5108843" "5134085" "5310446" "5354695" "5371399" "5391510" "5459346" "5471948" "5557122" "5561302" "5565697" "5571741" "5592007" "5592018" "5670798" "5679965" "5683934" "5840593" "5861651" "5880040" "5940736" "5946559" "5960297" "5989978" "6008126" "6025280" "6046464" "6066545" "6090684" "6107143" "6117722" "6133071" "6165383" "6221735" "6228694" "6246095" "6255169" "6261964" "6265317" "6274444" "6281532" "6284623" "6284626" "6319794" "6361885" "6362082" "6368931" "6403486" "6403975" "6406973" "6461936" "6476462" "6493497" "6498358" "6501121" "6506652" "6509618" "6521964" "6531369" "6531740" "6699764" "6855649").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/23 14:35
S41	452	crystalliz\$ near3 anneal\$3 near20 (heating or (temperature or heat or temp or degree) near2 (ramp or ramping or increase or increasing or increased or up))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/23 14:48
S42	71	438/479.ccls. and (strain or strained or straining or tensile or compressive or compressed) near2 (silicon or si)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/23 15:31

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S43	340	438/481.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/23 15:38
S44	608	438/509.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/23 16:04
S45	32	438/763.ccls. and (strain or strained or straining or tensile or compressive or compressed) near2 (silicon or si)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/23 16:19
S46	155	438/938.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/23 16:21
S47	465	257/616.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/23 16:31
S48	429	257/E29.193.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/23 16:46
S49	160	(silicon-on-insulator or soi or buried near insulator or buried near oxide) and (sige or silicon near germanium or si near ge or gesi) near4 (straining or (strain or stress) near3 (induc\$4 or generat\$4 or apply\$4 or match\$4 or application))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/23 16:57